

each of said dummy source lines respectively corresponding to said plurality of second data lines is provided as a wiring common to a corresponding one of said plurality of source lines, and

each of said dummy source line selection portions respectively corresponding to said dummy source lines is common to a corresponding one of said source selection portions.

18. (Amended) A thin film magnetic memory device, comprising:

a plurality of memory cells arranged in a matrix, each of said plurality of memory cells including a magnetic storage portion having its electric resistance value varying according to a storage data level written by combination of first and second data write magnetic fields;

a plurality of write word lines provided respectively corresponding to memory cell rows, and selectively activated in data write operation to pass therethrough a first data write current for generating said first data write magnetic field;

a plurality of source lines provided respectively corresponding to said memory cell rows, and coupled to a first voltage at their respective one ends;

a plurality of bit lines provided respectively corresponding to memory cell columns, and selectively receiving a second data write current for generating said second data write magnetic field in said data write operation according to a column selection result; and

a word line driver for coupling the activated write word line to a second voltage at its one end in said data write operation, wherein

said [second] first data write current flows through a current path formed from said activated write word line and at least one of said plurality of source lines which is electrically coupled to said activated write word line at the other ends.

22. (Amended) A thin film magnetic memory device, comprising:
a plurality of memory cells arranged in a matrix, each of said plurality of memory cells including

a magnetic storage portion having its electric resistance value varying according to a storage data level written therein by combination of first and second data write magnetic fields, and

an access portion coupled in series with said magnetic storage portion, and selectively turned ON in data read operation to pass a data read current therethrough and turned OFF in data write operation, said thin film magnetic memory device further comprising:

a plurality of read word lines provided respectively corresponding to memory cell rows, for turning ON said access portion in said data read operation according to a row selection result;

a plurality of write word lines provided respectively corresponding to said memory cell rows, and selectively activated to pass therethrough a first data write current generating said first data write magnetic field in said data write operation;

a plurality of bit lines provided respectively corresponding to memory cell columns, each of said plurality of bit lines being electrically coupled to said plurality of write word lines through said memory cells;